

1. Scope :

This specification applies to silicon zerocrossing phototriac chips,
Device No. ST-0181

2. Structure :

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

3. Size :

- 3-1. Chip size : 47.2 mils × 47.2 mils (1.200 mm ×1.200mm).
- 3-2. Chip thickness : 12 ± 1.0 mil (0.305 ± 0.025 mm).
- 3-3. Pad area : 5.9 mil × 5.5 mil (0.150 mm × 0.140 mm).
- 3-4. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	I_{DRM}	$V_{DRM}=800V$			100	nA
Peak on-state voltage	V_{TM}	$I_{TM}=100mA$		1.6	3	V
Critical rate of Rise voltage	dv/dt		1000			V/ μ S
Holding current	I_H			200		μ A
Inhibit Voltage	V_{INH}	$I_{DS}=10\mu A$		5	20	V

